

V414/V414A

HIGH VOLTAGE, PHOTO MOS RELAY

COSMO

FEATURES

- Normally Close, Single Pole Single Throw
- Control 400VAC or DC Voltage
- Switch 130mA Loads
- LED control Current, 5mA
- Low ON-Resistance
- $dv/dt, >500V/ms$
- Isolation Test Voltage, 3750VACrms

Absolute Maximum Ratings($T_a=25^{\circ}C$)

Emitter(Input)

Reverse Voltage	5.0V
Continuous Forward Current	50mA
Peak Forward Current	1A
Power Dissipation	100mW
Derate Linearly from 25°C	1.3mW/°C

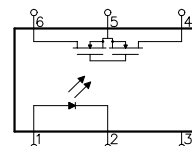
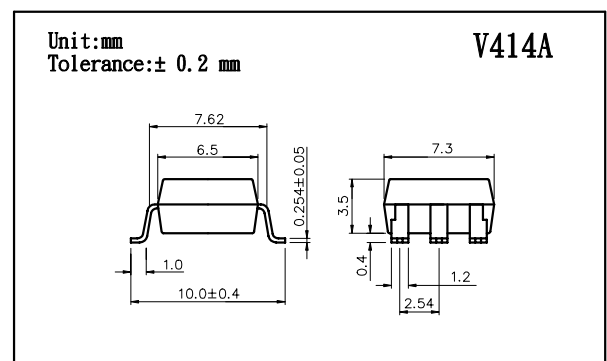
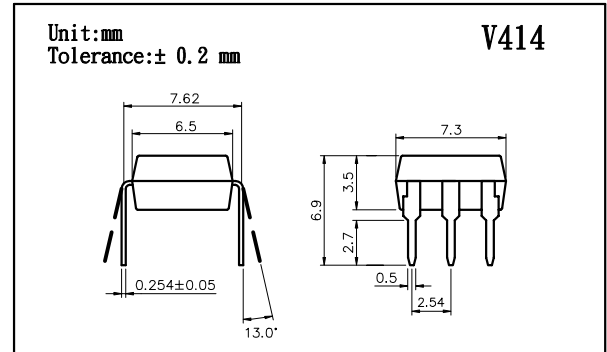
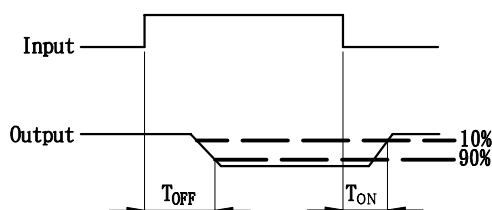
Detector(Output)

Output Breakdown Voltage	$\pm 400V$
Continuous Load Current	$\pm 130mA$
Power Dissipation	500mW

General Characteristics

Isolation Test Voltage	3750VACrms
Isolation Resistance $V_{io}=500V, T_a=25^{\circ}C$	$\geq 10^{10} \Omega$
Total Power Dissipation	550mW
Derate Linearly from 25°C	2.5mW/°C
Storage Temperature Range	-40°C to +125°C
Operating Temperature Range	-30°C to +85°C
Junction Temperature	100°C
Soldering Temperature, 2mm from case, 10 sec	260°C

● Operate/Reverse time



1 FORM B
NORMALLY CLOSED

V414/V414A

HIGH VOLTAGE, PHOTO MOS RELAY

Characterisitcs

(Ta=25°C)

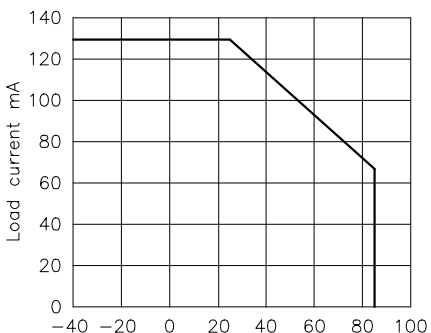
Description		Symbol	Min.	Typ.	Max.	Unit	Test Condition
Emitter(Input)							
Forward Voltage		VF		1.8	2.0	V	IF=10mA
Operation Input Current		I _{OFF}			5	mA	V _L =± 20V, I _L ≤5uA
Recovery Input Current		I _{ON}	0.2			mA	V _L =± 20V, I _L =100mA t=10mS
Detector (output)							
Output Breakdown Voltage		VB	400			V	I _B =50uA
Output Off-State Leakage		I _{T(OFF)}		0.2	2	uA	V _T =100V, I _F =10mA
I/O Capacitance		CISO		6		pF	I _F =0, f=1MHz
ON Resistance	Con- nection	A		40	50	Ω	I _L =100mA, I _F =0mA
		B	RON	20	25		
		C		10	12.5		
Reverse(ON) Time		TON		0.6	1.5	ms	I _F =10mA, V _L =± 20V
Operate(OFF) Time		TOFF		0.3	1.0	ms	t=10ms, I _L =± 100mA

Mos Relay Schematic and Wiring Diagrams

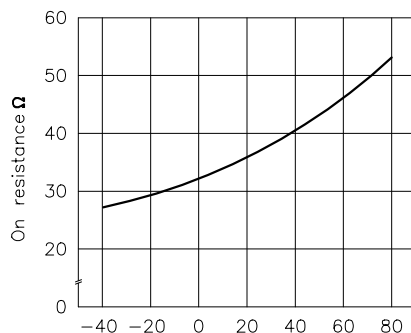
Type	Schematic	Output configuration	Load	Con- nection	Wiring Diagrams
V414 & V414A		1a	AC/DC	A	
			DC	B	
			DC	C	

DATA CURVE

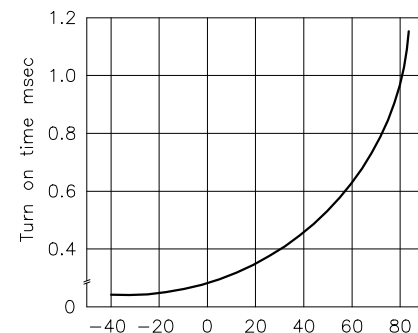
Load current vs. ambient temperature
Allowable ambient temperature:
-40°C to +85°C



On resistance vs. ambient temperature
Across terminals 4 and 6 pin
LED current: 0mA
Continuous load current: 130mA(DC)



Operate(OFF) time vs. ambient temperature:
Load voltage 400V(DC)
LED current: 5mA
Continuous load current: 130mA(DC)

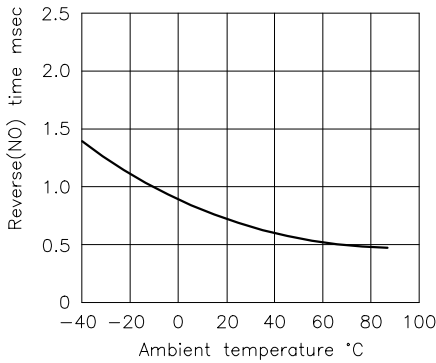


V414/V414A

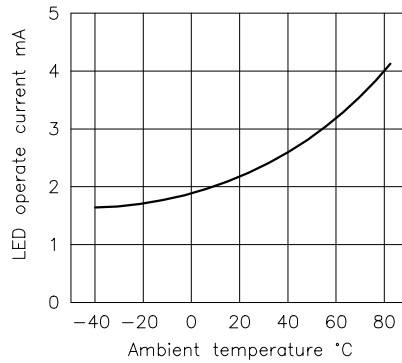
HIGH VOLTAGE, PHOTO MOS RELAY

V414/V414A

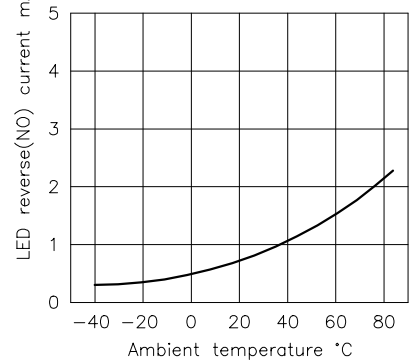
Reverse(NO) time vs. ambient temperature
LED current: 5mA; Load voltage: 400V(DC)
Continuous load current: 130mA(DC)



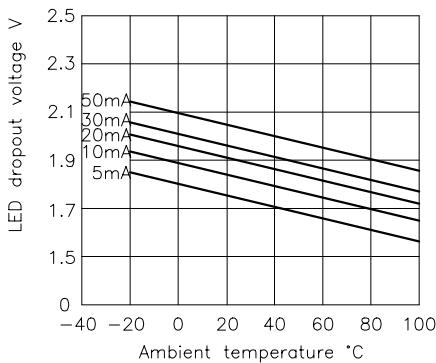
LED operate(OFF) vs. ambient temperature
Load voltage: 400V(DC)
Continuous load current: 130mA(DC)



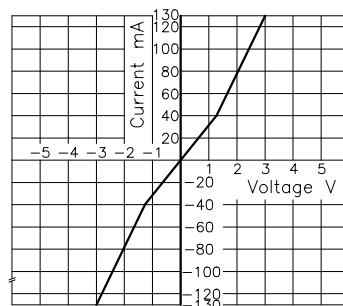
LED reverse(NO) current vs. ambient temperature
Load voltage: 400V(DC)
Continuous load current: 130mA(DC)



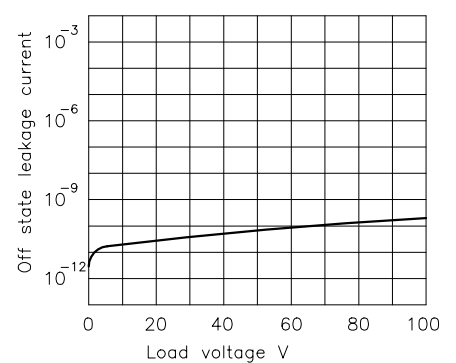
LED dropout voltage vs. ambient temperature
LED current: 5 to 50mA



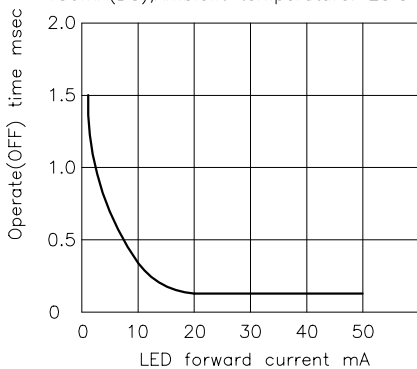
Voltage vs. current characteristics of output at MOS FET portion
Measured portion: across terminals 4 and 6 pin
Ambient temperature: 25°C



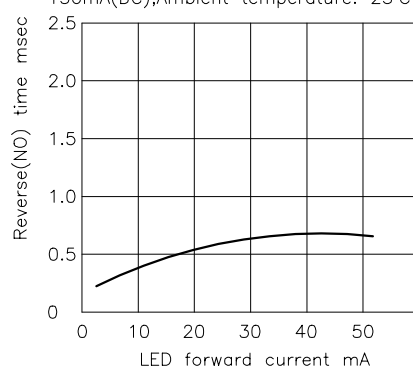
Off state leakage current
Across terminals 4 and 6 pin
Ambient temperature: 25°C



LED forward current vs. operate(OFF) time
Across terminals 4 and 6 pin; Load voltage: 400V(DC); Continuous load current: 130mA(DC); Ambient temperature: 25°C



LED forward current vs. reverse(NO) time
Across terminals 4 and 6 pin; Load voltage: 400V(DC); Continuous load current: 130mA(DC); Ambient temperature: 25°C



Applied voltage vs. output capacitance
Across terminals 4 and 6 pin
Frequency: 1MHz; Ambient temperature: 25°C

